Nihon Inter Electronics Corporation

THYRISTOR MODULE

PDT2008 PDH2008

200A / 800V

FEATURES

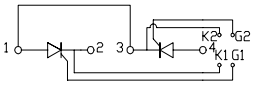
* Isolated Base
* Dual Thyristors or Thyristor and Diode Cascaded Circuit
* High Surge Capability
* UL Recognized, File No. E187184

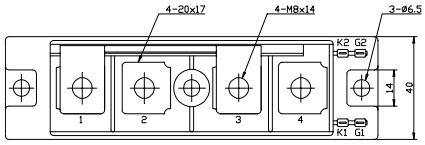
TYPICAL APPLICATIONS

* AC phase control

OUTLINE DRAWING

PDT





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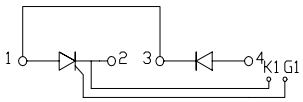
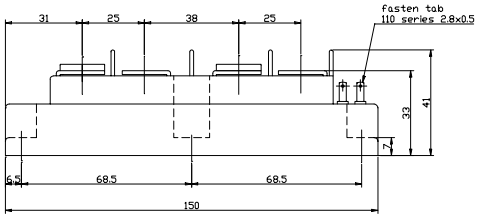




Approx Net Weight:480g

Maximum Ratings

Parameter	Symbol	Grade	Unit
		PDT/PDH2008	
Repetitive Peak Off-State Voltage	V_{DRM}	800	V
Non Repetitive Peak Off-State Voltage	V_{DSM}	960	
Repetitive Peak Reverse Voltage	V_{RRM}	800	V
Non Repetitive Peak Reverse Voltage	V_{RSM}	960	

arameter			Conditions	Max Rated Value	Unit
Average Rectified Output Current *1		$I_{O(AV)}$	50Hz Half Sine Wave condition Tc=65℃	200	A
RMS On-State Current		$I_{T(RMS)}$		314	A
Surge Forward Current		I_{FSM}	50 Hz Half Sine Wave,1cycle Non-Repetitive	4000	A
I Squared t		I^2t	2msec to 10msec	80000	A^2s
Critical Rate of Turned-On Current		di/dt	V_D=2/3V_{DRM}, I_{TM}=2·I_O, Tj=125℃ I_G=300mA, di_G/dt=0.2A/μs	100	A/μs
Peak Gate Power		P_{GM}		5	W
Average Gate Power		$P_{G(AV)}$		1	W
Peak Gate Current		I_{GM}		2	A
Peak Gate Voltage		V_{GM}		10	V
Peak Gate Reverse Voltage		V_{RGM}		5	V
Operating JunctionTemperature Range		Tjw		-40 to +125	℃
Storage Temperature Range		Tstg		-40 to +125	℃
Isoration Voltage		Viso	Base Plate to Terminals, AC1min	2000	V
Mounting torque	Case mounting	Ftor	M6 Screw	2.5 to 3.5	N•m
	Terminals		M8 Screw	9.0 to 10.0	

Value per 1 Arm

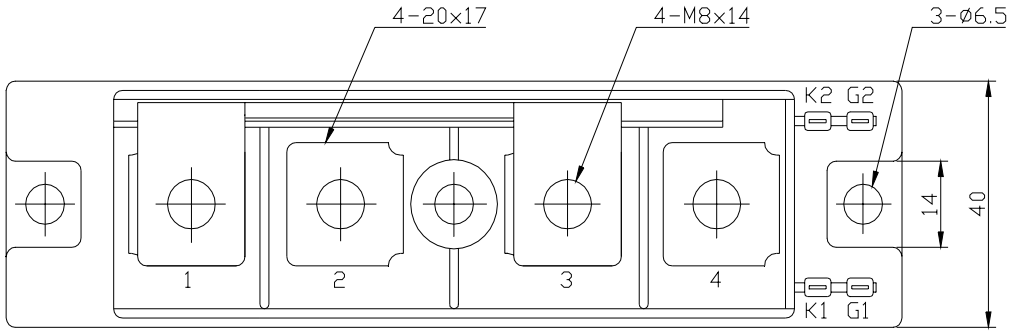
Electrical • Thermal Characteristics

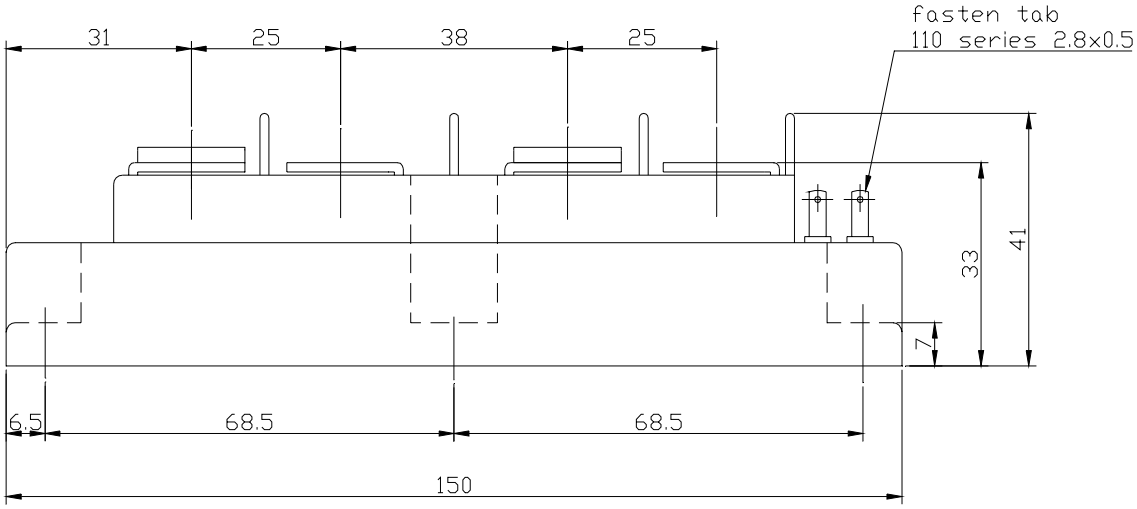
Characteristics	Symbol	Test Conditions		Maximum Value.			Unit
				Min.	Typ.	Max.	
Peak Off-State Current	I_{DM}	V_{DM}= V_{DRM}, Tj=125℃				30	mA
Peak Reverse Current	I_{RM}	V_{RM}= V_{RRM}, Tj= 125℃				30	mA
Peak On-State Voltage	V_{TM}	I_{TM}= 600A, Tj=25℃				1.34	V
Gate Current to Trigger	I_{GT}	V_D=6V,I_T=1A	Tj=-40℃			300	mA
			Tj=25℃			150	
			Tj=125℃			80	
Gate Voltage to Trigger	V_{GT}	V_D=6V,I_T=1A	Tj=-40℃			5	V
			Tj=25℃			3	
			Tj=125℃			2	
Gate Non-Trigger Voltage	V_{GD}	V_D=2/3V_{DRM} Tj=125℃		0.25			V
Critical Rate of Rise of Off-State Voltage	dv/dt	V_D=2/3V_{DRM} Tj=125℃		500			V/μs
Turn-Off Time	tq	I_{TM}=I_O,V_D=2/3V_{DRM} dv/dt=20V/μs, V_R=100V -di/dt=20A/μs, Tj=125℃			100		μs
Turn-On Time	tgt	Tj=25℃, I_{TM}=$I_{T(RMS)}$ V_D=2/3V_{DRM}, I_G=300mA di_G/dt=0.2A/μs			6		μs
Delay Time	td				2		μs
Rise Time	tr				4		μs
Latching Current	I_L	Tj=25℃			100		mA
Holding Current	I_H	Tj=25℃			60		
Thermal Resistance *1	Rth(j-c)	Junction to Case				0.23	℃/W
	Rth(c-f)	Base Plate to Heat Sink with Thermal Compound				0.1	

Value Per 1Arm

*1: Value Per Module

PDT/PDH2008 OUTLINE DRAWING (Dimensions in mm)





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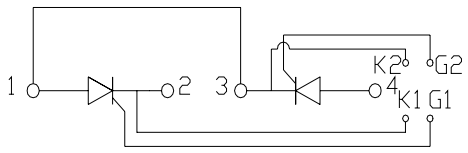

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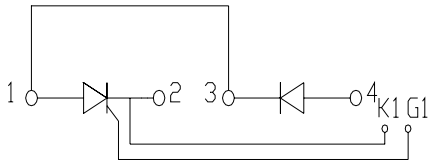
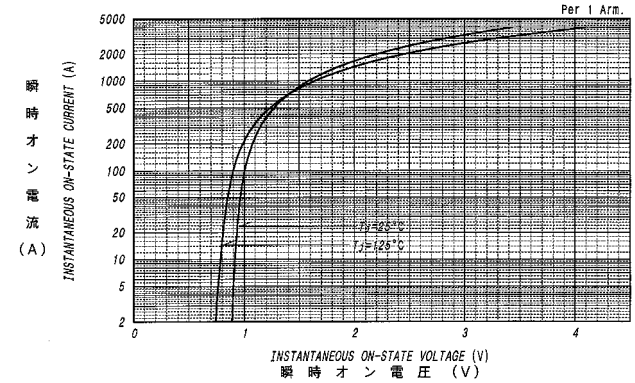
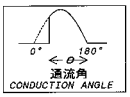
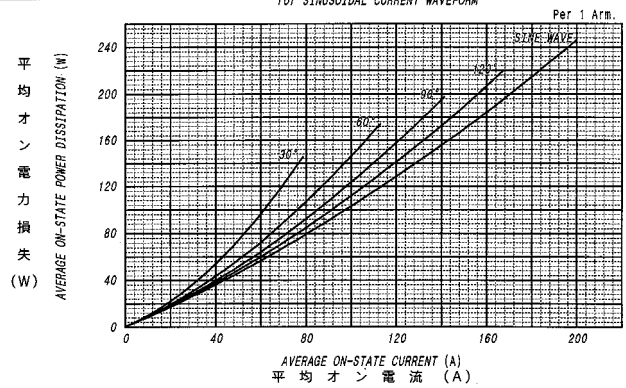


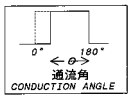
オン電圧特性
ON-STATE CURRENT VS. VOLTAGE



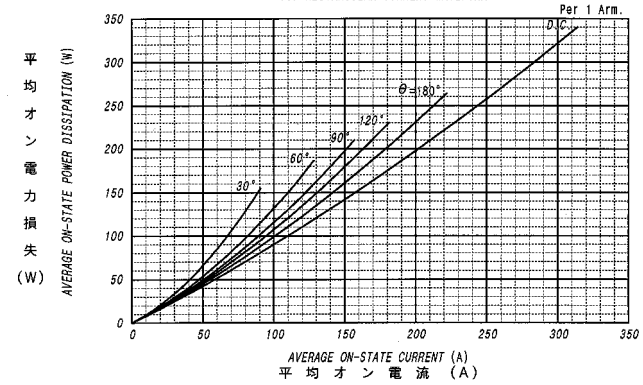


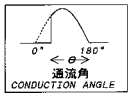
平均オン電力損失特性
AVERAGE ON-STATE POWER DISSIPATION
for SINUSOIDAL CURRENT WAVEFORM



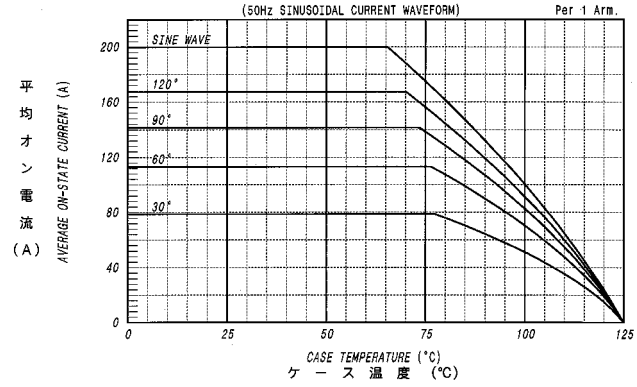


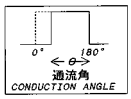
平均オン電力損失特性
AVERAGE ON-STATE POWER DISSIPATION
for RECTANGULAR CURRENT WAVEFORM



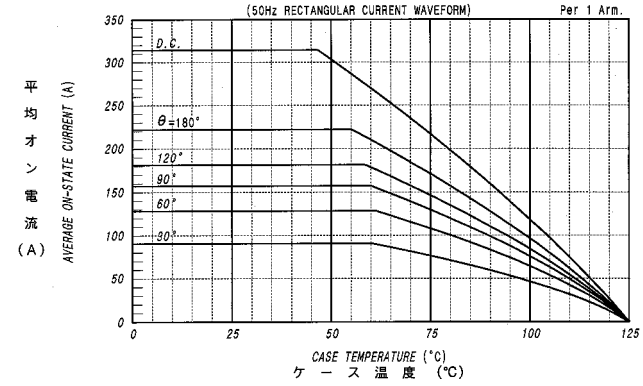


平均オン電流－ケース温度定格
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE



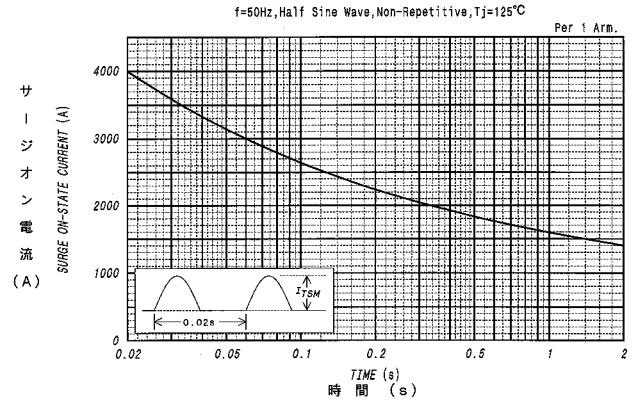


平均オン電流－ケース温度定格
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE

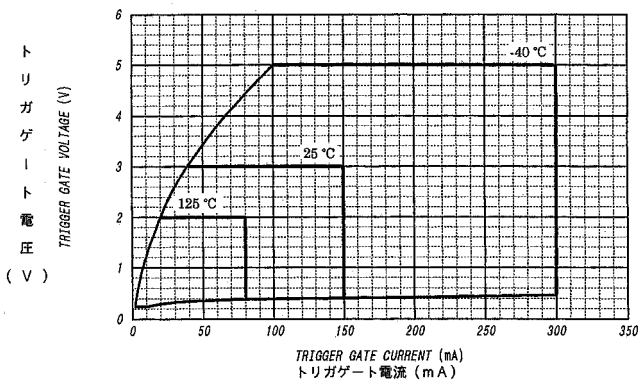


サージオン電流定格
SURGE CURRENT RATINGS

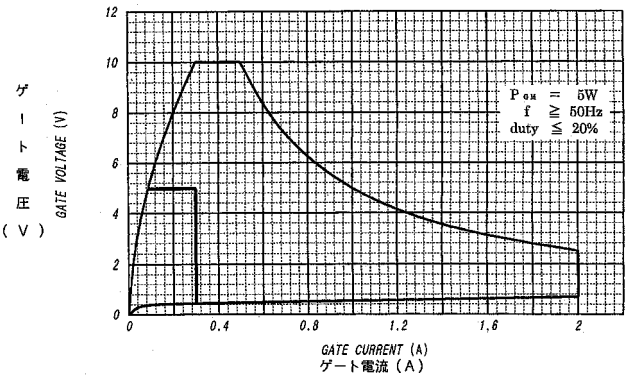
f=50Hz,Half Sine Wave,Non-Repetitive,Tj=125°C



ゲート特性
GATE CHARACTERISTCS



ゲート定格
GATE RATINGS



過渡熱抵抗特性
MAXIMUM TRANSIENT THERMAL IMPEDANCE